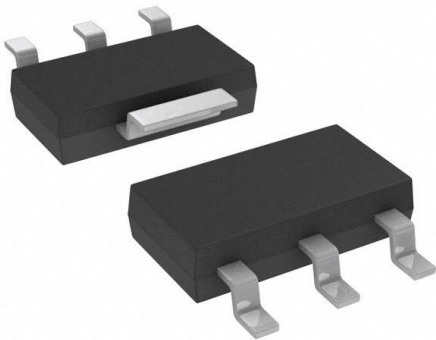


BCP 68-25 H6327 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

| | |
|------------------------------|---|
| DiGi Electronics Part Number | BCP 68-25 H6327-DG |
| Manufacturer | Infineon Technologies |
| Manufacturer Product Number | BCP 68-25 H6327 |
| Description | TRANS NPN 20V 1A SOT223-4 |
| Detailed Description | Bipolar (BJT) Transistor NPN 20 V 1 A 100MHz 3 W S urface Mount PG-SOT223-4 |



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

BCP 68-25 H6327

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

20 V

Current - Collector Cutoff (Max):

100nA (ICBO)

Power - Max:

3 W

Operating Temperature:

150°C (TJ)

Package / Case:

TO-261-4, TO-261AA

Base Product Number:

BCP 68

Manufacturer:

Infineon Technologies

Product Status:

Discontinued at Digi-Key

Current - Collector (Ic) (Max):

1 A

Vce Saturation (Max) @ Ib, Ic:

500mV @ 100mA, 1A

DC Current Gain (hFE) (Min) @ Ic, Vce:

160 @ 500mA, 1V

Frequency - Transition:

100MHz

Mounting Type:

Surface Mount

Supplier Device Package:

PG-SOT223-4

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0075

Moisture Sensitivity Level (MSL):

1 (Unlimited)

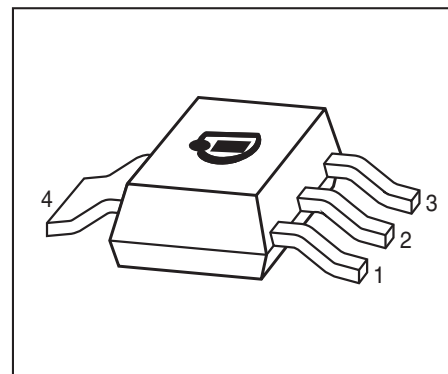
ECCN:

EAR99



NPN Silicon AF Transistor

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary type: BCP69 (PNP)
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



| Type | Marking | Pin Configuration | | | | | | Package |
|----------|---------|-------------------|-----|-----|-----|---|---|---------|
| | | 1=B | 2=C | 3=E | 4=C | - | - | |
| BCP68-25 | * | 1=B | 2=C | 3=E | 4=C | - | - | SOT223 |

* Marking is the same as the type-name

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|-----------|-------------|------|
| Collector-emitter voltage | V_{CEO} | 20 | V |
| Collector-emitter voltage | V_{CES} | 25 | |
| Collector-base voltage | V_{CBO} | 25 | |
| Emitter-base voltage | V_{EBO} | 5 | |
| Collector current | I_C | 1 | A |
| Peak collector current, $t_p \leq 10$ ms | I_{CM} | 2 | |
| Base current | I_B | 100 | mA |
| Peak base current | I_{BM} | 200 | |
| Total power dissipation- $T_S \leq 114$ °C | P_{tot} | 3 | W |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -65 ... 150 | |

¹⁾Pb-containing package may be available upon special request



Thermal Resistance

| Parameter | Symbol | Value | Unit |
|--|------------|-----------|------|
| Junction - soldering point ¹⁾ | R_{thJS} | ≤ 12 | K/W |

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|-----------|--------|--------|------|------|------|
| | | min. | typ. | max. | |

DC Characteristics

| | | | | | |
|---|---------------|-----------------|---------------|---------------|---------------|
| Collector-emitter breakdown voltage $I_C = 30 \text{ mA}, I_B = 0$ | $V_{(BR)CEO}$ | 20 | - | - | V |
| Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$ | $V_{(BR)CBO}$ | 25 | - | - | |
| Collector-emitter breakdown voltage $I_C = 10 \mu\text{A}, V_{BE} = 0$ | $V_{(BR)CES}$ | 25 | - | - | |
| Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$ | $V_{(BR)EBO}$ | 5 | - | - | |
| Collector-base cutoff current $V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$ | I_{CBO} | - | - | 0.1 100 | μA |
| DC current gain ²⁾ $I_C = 5 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 1 \text{ A}, V_{CE} = 1 \text{ V}$ | h_{FE} | 50 160 60 | - 250 - | - 375 - | - |
| Collector-emitter saturation voltage ²⁾ $I_C = 1 \text{ A}, I_B = 100 \text{ mA}$ | V_{CEsat} | - | - | 0.5 | V |
| Base-emitter voltage ²⁾ $I_C = 5 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 1 \text{ A}, V_{CE} = 1 \text{ V}$ | $V_{BE(ON)}$ | - | 0.6 - | - 1 | |

AC Characteristics

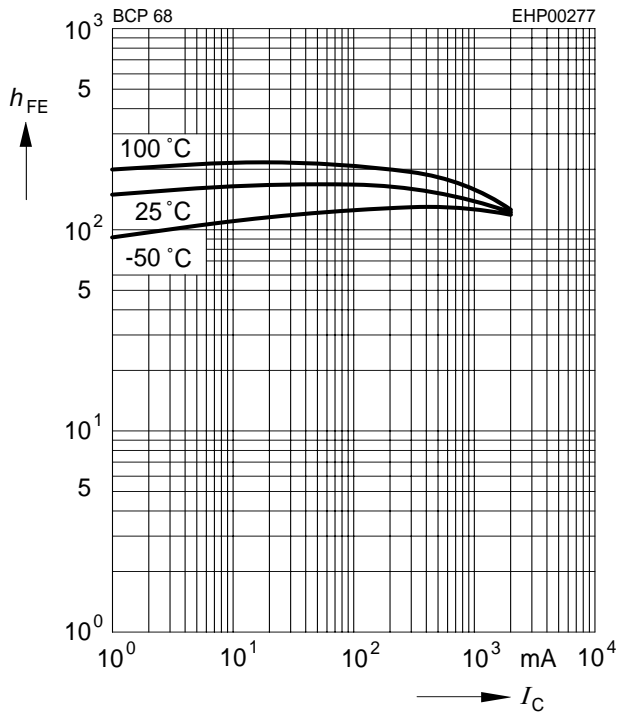
| | | | | | |
|---|-------|---|-----|---|-----|
| Transition frequency $I_C = 100 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$ | f_T | - | 100 | - | MHz |
|---|-------|---|-----|---|-----|

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

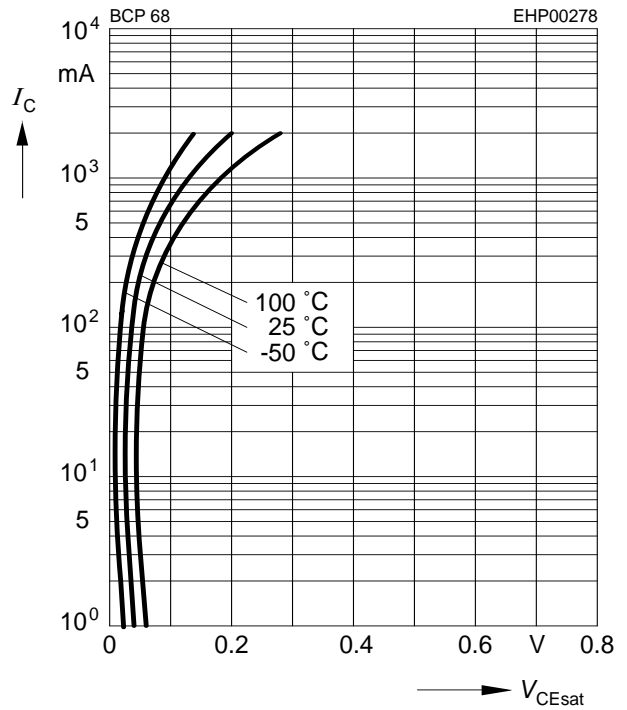
²⁾Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

DC current gain $h_{FE} = f(I_C)$

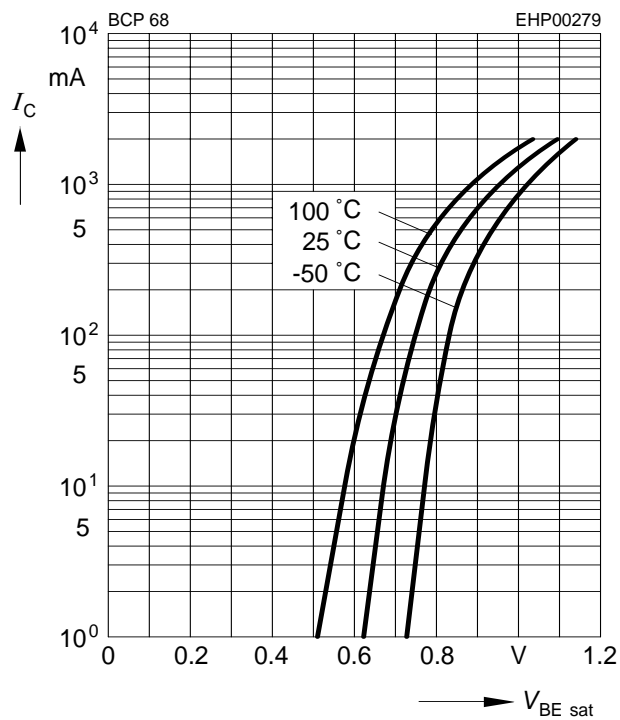
$V_{CE} = 1 \text{ V}$

**Collector-emitter saturation voltage**

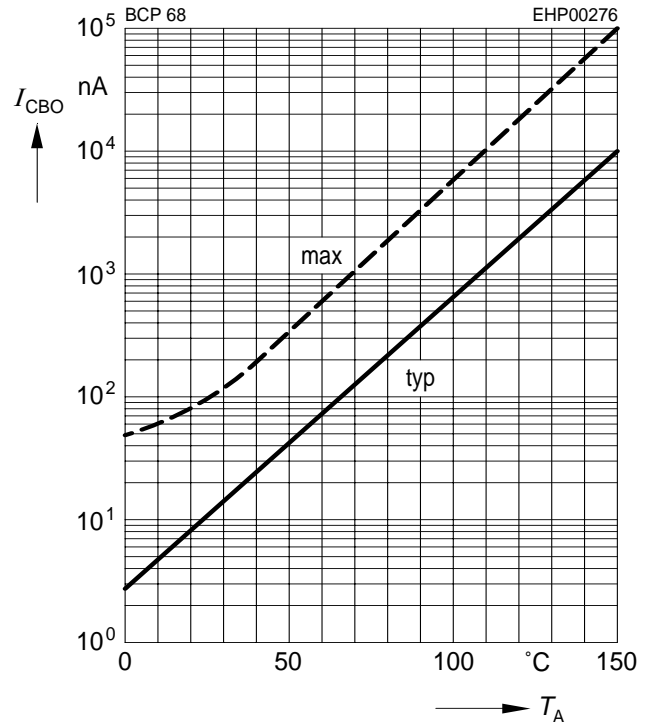
$I_C = f(V_{CEsat}), h_{FE} = 10$

**Base-emitter saturation voltage**

$I_C = f(V_{BEsat}), h_{FE} = 10$

**Collector cutoff current $I_{CBO} = f(T_A)$**

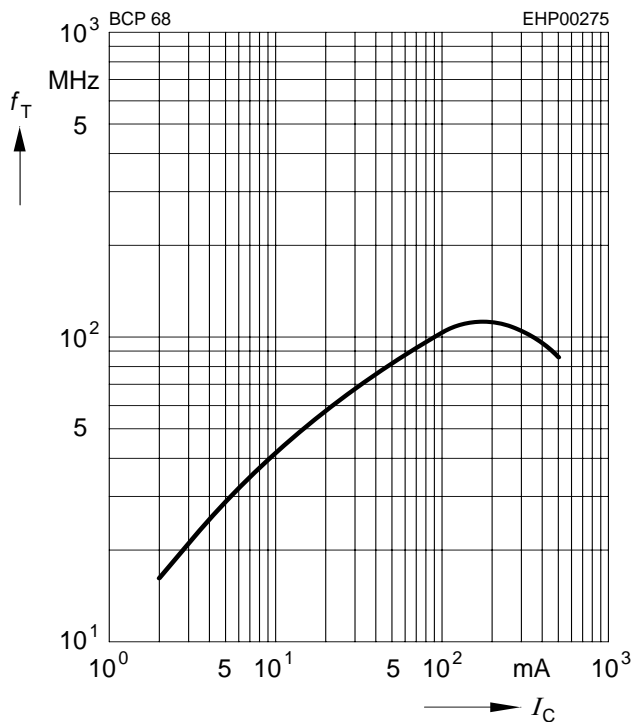
$V_{CBO} = 25 \text{ V}$



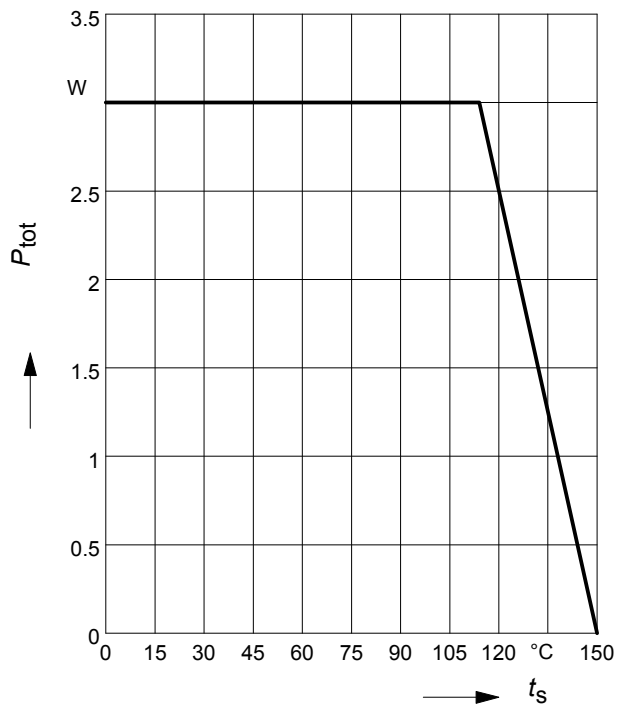


Transition frequency $f_T = f(I_C)$

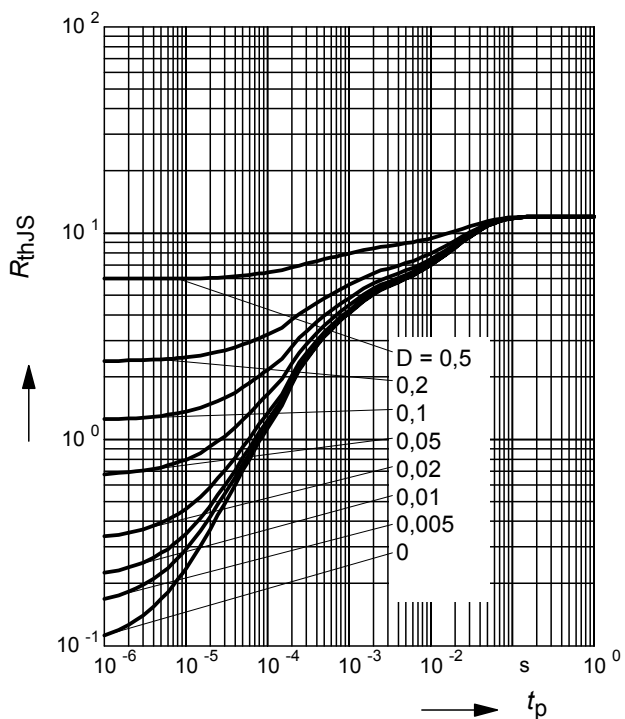
$V_{CE} = 5\text{ V}$



Total power dissipation $P_{tot} = (T_S)$

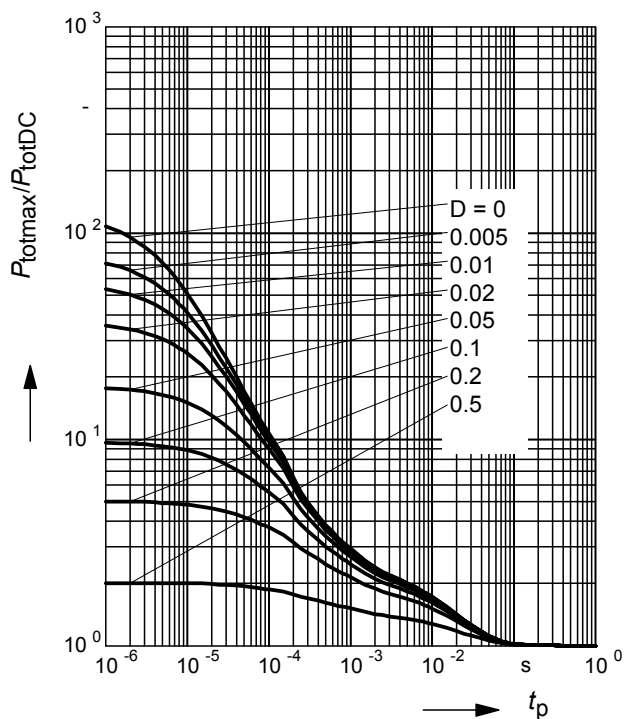


Permissible Pulse Load $R_{thJS} = f(t_p)$



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

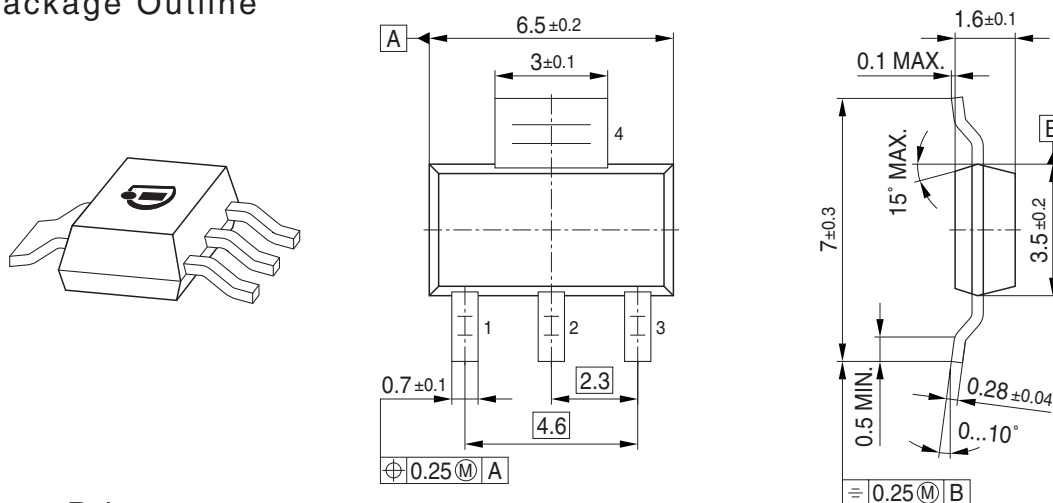




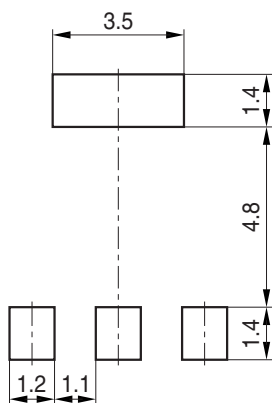
Package SOT223

BCP68-25

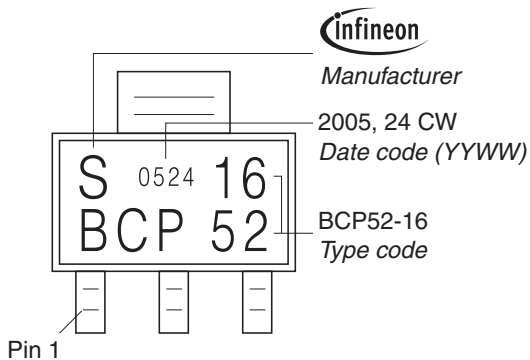
Package Outline



Foot Print

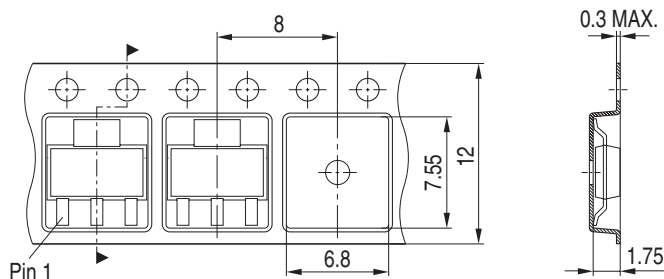


Marking Layout (Example)



Packing

Reel ø180 mm = 1.000 Pieces/Reel
 Reel ø330 mm = 4.000 Pieces/Reel





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